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#### **40V N-CHANNEL ENHANCEMENT MODE MOSFET**

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = 25°C
40V	30mΩ @ V <sub>GS</sub> = 10V	13.7A
	50mΩ @ V <sub>GS</sub> = 4.5V	10.6A

# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- · Power management functions

### **Features and Benefits**

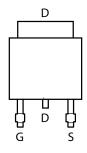
- Low on-resistance
- · Fast switching speed
- "Green" component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

# **Mechanical Data**

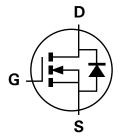
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)







PIN OUT -TOP VIEW



Equivalent Circuit

### Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
DMN4030LK3-13	N4030L	13	16	2,500	

Notes: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

# **Marking Information**



Oll = Manufacturer's Marking
N4030L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01 - 53)





## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage			$V_{DSS}$	40	V
Gate-Source voltage (Note 2)			V <sub>GS</sub> ±20		V
		(Note 4)	I <sub>D</sub>	13.7	
Continuous Drain current	$V_{GS} = 10V$	$T_A = 70^{\circ}C \text{ (Note 4)}$		10.9	Α
		(Note 3)		9.4	
Pulsed Drain current $V_{GS} = 10V$ (Note 5		(Note 5)	$I_{DM}$	37.7	Α
Continuous Source current (Body diode) (Note 4)		I <sub>S</sub>	10.7	Α	
Pulsed Source current (Body diode) (Note 5)		I <sub>SM</sub>	37.7	А	

## Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Note 3)		4.18 33.4		
Power dissipation Linear derating factor	(Note 4)	$P_{D}$	8.9 71.4	W mW/°C	
	(Note 6)		2.14 17.1		
The word Designation to Austrian	(Note 3)		29.9		
Thermal Resistance, Junction to Ambient	(Note 4) (Note 6)	$R_{ hetaJA}$	14.0 58.4	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	2.46		
Operating and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	

#### Notes:

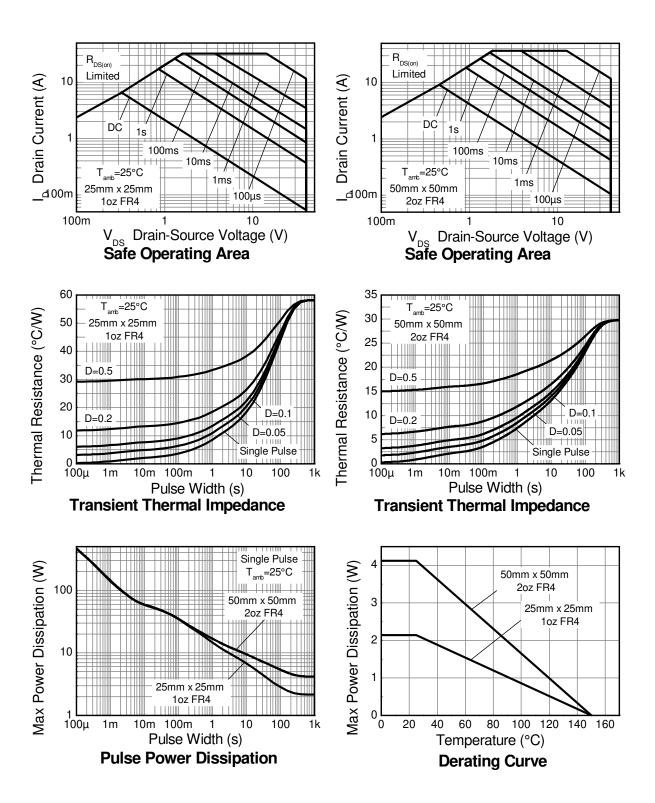
- 2. AEC-Q101  $V_{\text{GS}}$  maximum is  $\pm 16V$ .
- 3. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 4. Same as note 3, except the device is measured at  $t \le 10$  sec.
- 5. Same as note 3, except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.

  6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Thermal resistance from junction to solder-point (at the end of the drain lead).





### **Thermal Characteristics**







# Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Co	ndition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_		V	$I_D = 250 \mu A, V_{GS} = 100 \mu A$	= 0V
Zero Gate Voltage Drain Current	IDSS	_	_	0.5	μΑ	$V_{DS} = 40V, V_{GS} =$	= 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS}$	= 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	1.0		3.0	V	$I_D = 250 \mu A, V_{DS} = 100 \mu A$	= V <sub>GS</sub>
Static Drain Source On Decistones (Note 9)			0.021	0.030	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A	
Static Drain-Source On-Resistance (Note 8)	R <sub>DS (ON)</sub>	_	0.037	0.050	77	$V_{GS} = 4.5V, I_{D} = 0.00$	6A
Forward Transconductance (Notes 8 & 9)	9 <sub>fs</sub>	_	22.8	_	S	$V_{DS} = 15V, I_{D} = 1$	2A
Diode Forward Voltage (Note 8)	$V_{SD}$	_	0.95	1.1	V	$I_S = 12A, V_{GS} = 0$	V
Reverse recovery time (Note 9)	t <sub>rr</sub>		135	_	ns	I <sub>S</sub> = 12A, di/dt = 100A/μs	
Reverse recovery charge (Note 9)	Q <sub>rr</sub>		799	_	nC		
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	604	_	pF	V 00V V	0)/
Output Capacitance	Coss		106		pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = -f= 1MHz	= UV
Reverse Transfer Capacitance	C <sub>rss</sub>		59.6	_	рF	1= 1101112	
Total Gate Charge (Note 10)	$Q_g$	_	6.5	_	nC	$V_{GS} = 4.5V$	
Total Gate Charge (Note 10)	$Q_g$	_	12.9	_	nC		$V_{DS} = 20V$
Gate-Source Charge (Note 10)	Q <sub>gs</sub>	_	2.3	_	nC	$V_{GS} = 10V$	I <sub>D</sub> = 12A
Gate-Drain Charge (Note 10)	Q <sub>gd</sub>	_	3.6	_	nC	1	
Turn-On Delay Time (Note 10)	t <sub>D(on)</sub>	_	4.2	_	ns	·	
Turn-On Rise Time (Note 10)	t <sub>r</sub>	_	12.4	_	ns	$V_{DD} = 20V, V_{GS} = 10V$	
Turn-Off Delay Time (Note 10)	t <sub>D(off)</sub>	_	13.8	_	ns	$I_D = 12A, R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 10)	t <sub>f</sub>		10.7	_	ns		

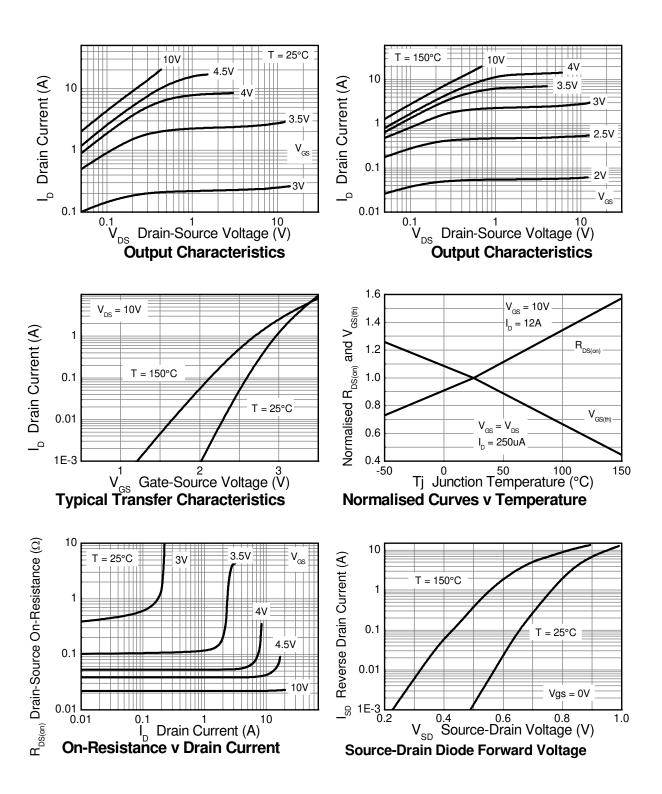
Notes:

- 8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq 2\%$
- Wedsdied that passed conditions. False width 2 600µs, day cycle 2 276
   For design aid only, not subject to production testing.
   Switching characteristics are independent of operating junction temperatures.



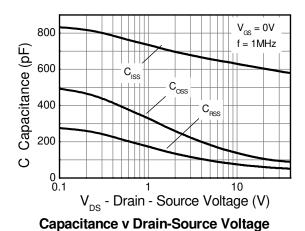


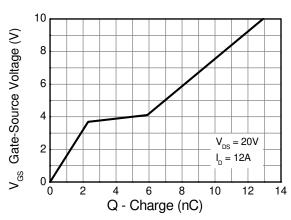
# **Typical Characteristics**





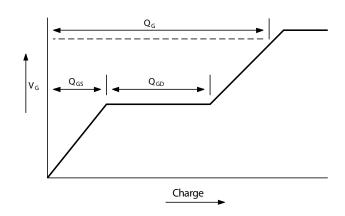
# **Typical Characteristics - continued**





Gate-Source Voltage v Gate Charge

## **Test Circuits**



Current regulator

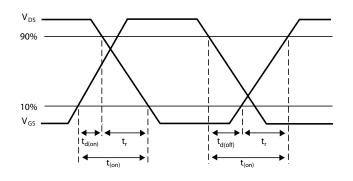
12V 0.2 \( \mu \). F 50k D.U.T

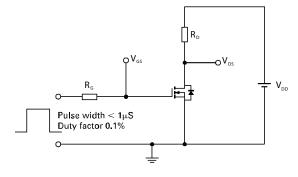
Vos

Vos

Basic gate charge waveform

Gate charge test circuit





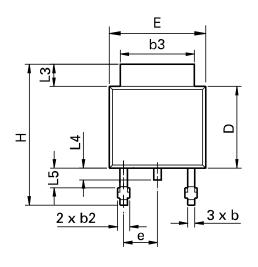
Switching time waveforms

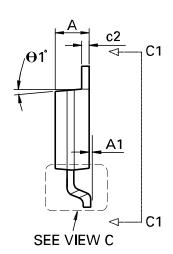
Switching time test circuit

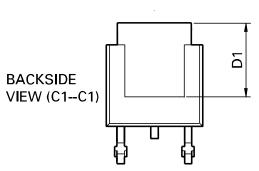


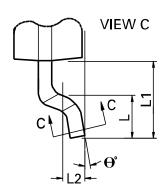


# **Package Outline Dimensions**







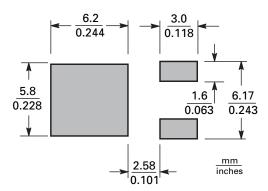


DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
<b>A</b> 1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-





### **Suggested Pad Layout**



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